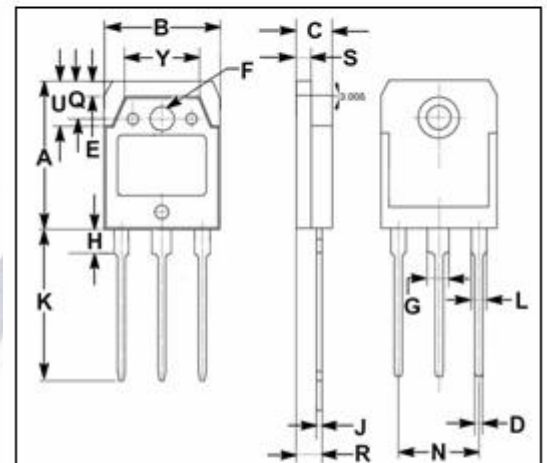
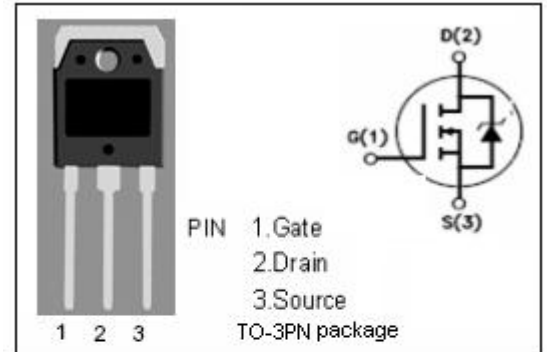


isc N-Channel MOSFET Transistor
AOK22N50L
DESCRIPTION

- Drain Current $-I_D=22A@ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=500V(\text{Min})$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed especially for high voltage, high speed applications, such as off-line switching power supplies , UPS, AC and DC motor controls, relay and solenoid drivers.


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $TC=25^\circ C$	22	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	417	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

isc N-Channel Mosfet Transistor**AOK22N50L****• ELECTRICAL CHARACTERISTICS (T_c=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 0.25mA	500			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = 5V; I _D = 0.25mA	3.4		4.5	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =11A			0.26	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			± 100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =500V; V _{GS} = 0			1	μA
V _{SD}	Diode forward voltage	I _{DR} =1A, V _{GS} = 0 V			1.0	V